TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

262,144-WORD BY 36-BIT SYNCHRONOUS NO-TURNAROUND STATIC RAM

DESCRIPTION

The TC55VD836FF is a synchronous static random access memory (SRAM) organized as 262,144 words by 36 bits. NtRAMTM(no-turnaround SRAM) offers high bandwidth by eliminating dead cycles during the transition from a read to a write and vice versa. All inputs except Output Enable \overline{OE} and the Snooze pin ZZ are synchronized with the rising edge of the CLK input. A Read operation is initiated by the ADV Address Advanced Input signal; the input from the address pins and all control pins except the \overline{OE} and ZZ pins are loaded into the internal registers on the rising edge of CLK in the cycle in which ADV is asserted. The output data is available two clock cycles later. Write operations are internally self-timed and are initiated by the rising edge of CLK in the cycle in which ADV is asserted. The input from the address pins and all control pins except the \overline{OE} and ZZ pins are loaded into the internal registers on the rising edge of CLK in the cycle in which ADV is asserted. Input data is loaded in the third cycle after the cycle in which ADV is asserted. Byte Write Enables ($\overline{BW1}$ to $\overline{BW4}$) allow from one to four Byte Write operations to be performed. A 2-bit burst address counter and control logic are integrated into this SRAM. The TC55VD836FF uses a single power supply (3.3 V) or dual power supplies (3.3 V for core and 2.5 V for output buffer) and is available in a 100-pin low-profile plastic QFP (LQFP).

FEATURES

- Organized as 262,144 words by 36 bits
- Fast cycle time of 6.6 ns minimum (150 MHz maximum)
- Fast access time of 3.8 ns maximum (from clock edge to data output)
- No-turnaround operation with pipeline data output
- 2-bit burst address counter (support for interleaved or linear burst sequences)
- Synchronous self-timed Write
- Byte Write control
- Snooze mode pin (ZZ) for power down
- LVTTL-compatible interface
- Single power supply (3.3 V) or Dual power supplies (3.3 V for core and 2.5 V for output buffer)
- Available in 100-pin LQFP package (LQFP100-P-1420-0.65K; pitch:0.65 mm, height:1.6 mm, weight:0.56 grams (typical))

PIN ASSIGNMENT (TOP VIEW)

99 97 95 93 91 89 87 85 83 81 100 98 96 94 92 90 88 86 84 82 VDDQ | 4 Vssq | 5 I/O19 | 6 I/O20 | 7 I/O21 | 8 77 VDDQ 76 VSSQ 75 1/014 74III I/O13 73⊞ I/O12 I/O22 III 9 72III |/O11 Vssq III 10 VDDQ III 11 71⊞ Vsso 70 VDDQ I/O23 🖂 69HII I/O10 I/O24 13 VDD 14 V_{DD} □□ 65 VDD 64 ZZ 63 I/O8 i/O26 III VDDQ 20 VssQ 21 1/027 💷 22 59Ш 1/06 I/O28 💷 23 58 1/05 I/O29 TTT 24 57 III I/O4 I/O30 = 25 56¹¹¹ I/O3 Vsso □□ 26 55⊞ Vsso 54 VDDQ VDDQ III 27 I/O31 III 28 53 1/02 32 34 36 38 40 42 44 46 48 50

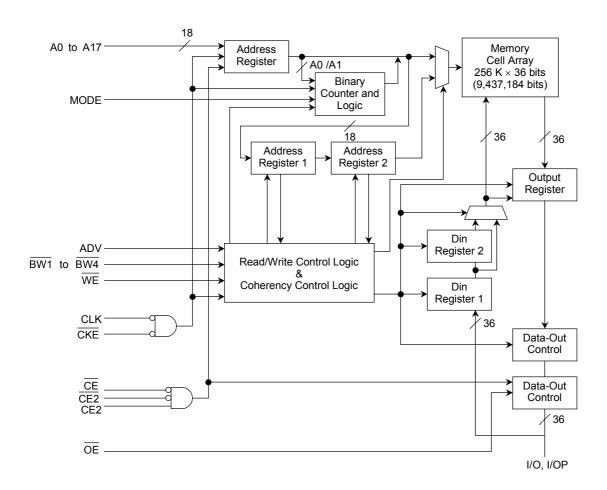
PIN NAMES

CLK	Clock Input					
A0 to A17	Address Inputs					
CE, CE2, CE2	Chip Enable Inputs					
ŌĒ	Output Enable Input					
WE	Write Enable input					
BW1 to BW4	Byte Write Enable					
ADV	Address Advance Input					
CKE	Clock Enable					
ZZ	Snooze Input					
I/O1 to I/O32	Data Inputs/Outputs					
I/OP1 to I/OP4	Parity Data Inputs/Outputs					
MODE	Mode select Input					
NC	No Connection					
NU	Not Usable					
V_{DD}	Power Supply for Core					
V_{DDQ}	Power Supply for Output Buffer					
V_{SS}	Ground for Core					
V_{SSQ}	Ground for Output Buffer					
TM	·					

Note: NtRAMTM and No-Turnaround Random Access Memory are trademarks of Samsung Electronics Co., Ltd..



BLOCK DIAGRAM





PIN DESCRIPTIONS

PIN NUMBER	SYMBOL	TYPE	DESCRIPTION
89	CLK	Input (NA)	Clock Input All synchronous input signals are registered on the rising edge of CLK. When the chip is enabled, address inputs and control pins except for OE and ZZ must meet the specified setup and hold times with respect to the CLK rising edge.
37, 36, 35, 34, 33, 32, 100, 99, 82, 81, 44, 45, 46, 47, 48, 49, 50, 83	A0 to A17	Input (synchronous)	Address Inputs These address inputs are registered on the rising edge of CLK. When the chip is enabled, address inputs must meet the specified setup and hold times with respect to the CLK rising edge.
98	CE	Input (synchronous)	Chip Enable Input This active-Low signal controls the chip status (enabled or disabled). It is sampled only when a new external address is loaded.
92	CE2	Input (synchronous)	Chip Enable Input This active-Low signal controls the chip status (enabled or disabled). It is sampled only when a new external address is loaded.
97	CE2	Input (synchronous)	Chip Enable Input This active-High signal controls the chip status (enabled or disabled). It is sampled only when a new external address is loaded.
86	ŌĒ	Input (asynchronous)	Output Enable Input This active-Low signal controls all 36 bits of the I/O output buffer.
88	WE	Input (synchronous)	Write Enable Input This active-Low input controls Read/Write operations.
93, 94, 95, 96	BW1 to BW4	Input (synchronous)	Byte Write Enable These active-Low inputs control Byte Write operations when a Write cycle is active. A Byte Write pin controls I/O pins as follows. BW1: I/O1 to I/O8, I/OP1 BW2: I/O9 to I/O16, I/OP2 BW3: I/O17 to I/O24, I/OP3 BW4: I/O25 to I/O32, I/OP4
85	ADV	Input (synchronous)	Address Advance Input This is used to load the internal registers with the input from the address and control signals when it is Low on the rising edge of CLK. When it is High, the internal burst address counter is incremented. The external address inputs are ignored when this signal is High.
87	CKE	Input (synchronous)	Clock Enable When High, CLK input is ignored and outputs retain the same state.
64	ZZ	Input (asynchronous)	Snooze Input This active-High signal is used to place the device into Sleep Mode (Low-Power Standby Mode). When Low, the device remains in the Active state. When High, the device goes into the Sleep state and memory data is retained. After this signal has been de-asserted, the device will wake up when a read or write operation is initiated by ADV.

PIN NUMBER	SYMBOL	TYPE	DESCRIPTION
52, 53, 56, 57, 58, 59, 62, 63, 68, 69, 72, 73, 74, 75, 78, 79, 2, 3, 6, 7, 8, 9, 12, 13, 18, 19, 22, 23, 24, 25, 28, 29	I/O1 to I/O32	I/O (synchronous)	Data Input/Output
51, 80, 1, 30	I/OP1 to I/OP4	I/O (synchronous)	Parity Data Input/Output
31	MODE	Input (synchronous)	Mode Select Input This signal selects the burst sequence. When High, the burst sequence is interleaved. When Low, it is linear.
39, 42, 43, 84	NC	NC	Not Connected
38	NU	Input (asynchronous)	Not Usable
14, 15, 16, 41, 65, 66, 91	VDD	Supply	Power Supply for Core
4, 11, 20, 27, 54, 61, 70, 77	VDDQ	Supply	Power Supply for Output Buffers
17, 40, 67, 90	VSS	Ground	Ground for Core
5, 10, 21, 26, 55, 60, 71, 76	VSSQ	Ground	Ground for Output Buffers



OPERATING MODE

(1) Synchronous Input Truth Table

OPERATION	WE	ADV	CE	BW	Addr. Used	CKE	ZZ	I/O (2 cycles later)
Read (begin burst)	Н	L	Select	Х	External	L	L	Output
Read (continue burst)	Х	Н	Х	Х	Internal	L	L	Output
Write (begin burst)	L	L	Select	L	External	L	L	Input
Write (continue burst)	Х	Н	Х	L	Internal	L	L	Input
NOP/Write Abort (begin burst)	L	L	Select	Н	Х	L	L	Hi-Z
Write Abort (continue burst)	Х	Н	Х	Н	Internal	L	L	Hi-Z
Deselected	Х	L	Deselect	Х	Х	L	L	Hi-Z
Deselect Continue (Note 2)	Х	Н	Х	Х	Х	L	L	Hi-Z
Ignore Clock Edge (Note 3)	Х	Х	Х	Х	Х	Н	L	Previous value
Snooze	Х	Х	X	Х	Х	Х	Н	Hi-Z

Notes: 1. H means logical High and L means logical Low. X means Don't care.

- 2. A Deselect Continue cycle can only be entered if a Deselect cycle is executed before it.
- 3. When the Ignore Clock Edge command is asserted during a Read operation, the output data for the previous cycle still appear on the I/O pins. When the command is asserted during a Write operation, the I/O pins remain at Hi-Z and the Write operation is not executed.
- 4. All synchronous Inputs must exhibit adequate setup and hold times either side of the rising edge of the CLK pin.
- 5. ZZ input is asynchronous, but is included is this table.

(2) Write Enable Truth Table

OPERATION	WE	BW1	BW2	BW3	BW4	I/O1 to I/O8 I/OP1	I/O9 to I/O16 I/OP2	I/O17 to I/O24 I/OP3	I/O25 to I/O32 I/OP4
Read	Н	Х	Х	Х	Х	Output	Output	Output	Output
	L	L	L	L	L	Input	Input	Input	Input
	L	L	Н	Н	Н	Input	Hi-Z	Hi-Z	Hi-Z
Write	L	Н	L	Н	Н	Hi-Z	Input	Hi-Z	Hi-Z
vviite	L	Н	Н	L	Н	Hi-Z	Hi-Z	Input	Hi-Z
	L	Н	Н	Н	L	Hi-Z	Hi-Z	Hi-Z	Input
	L	Н	Н	Н	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z

Notes: 1. H means logical High and L means logical Low. X means Don't care.

2. The status for I/O pins described in this column appears two clock cycles after the cycle in which the Read or Write command is asserted.

(3) Asynchronous Inputs Truth Table

OPERATION	ŌĒ	ZZ	I/O
Read	L	L	Dout
Neau	Н	L	Hi-Z
Write	X	L	Din, Hi-Z
Stop clock (Note 2)	Н	L	Hi-Z
Stop clock (Note 2)	L	L	Low-Z
Snooze (Note 3)	X	Н	Hi-Z

Notes: 1. H means logical High and L means logical Low. X means Don't care.

- 2. The Stop CLK Mode achieves Low-Power Standby by stopping the input clock.
- 3. The Snooze Mode achieves Low-Power Standby by asserting the ZZ pin.
- 4. The cycle immediately prior to a Snooze brought about by the ZZ pin must be a Read Mode or Deselect Mode cycle.
- 5. Memory data is retained during Snooze Mode cycles.



(4) Burst Sequence

MODE PIN	BURST OPERATION
L	Linear burst order
H or NC	Interleaved burst order

a) Linear Burst Sequence (MODE input = V_{SS})

Bit Order : A_{17} ----- A_1 A_0

1st Address (external)	2nd Address (internal)	3rd Address (internal)	4th Address (internal)
XX XX00	XX XX01	XX XX10	XX XX11
XX XX01	XX XX10	XX XX11	XX XX00
XX XX10	XX XX11	XX XX00	XX XX01
XX XX11	XX XX00	XX XX01	XX XX10

b) Interleaved Burst Sequence (MODE input = V_{DD} or NC)

Bit Order : A_{17} ----- A_1 A_0

1st Address (external)	2nd Address (internal)	3rd Address (internal)	4th Address (internal)
XX XX00	XX XX01	XX XX10	XX XX11
XX XX01	XX XX00	XX XX11	XX XX10
XX XX10	XX XX11	XX XX00	XX XX01
XX XX11	XX XX10	XX XX01	XX XX00

DEVICE OPERATION

(1) Read Operation

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌĒ	CKE	I/O	OPERATION
n	A0	Н	Х	L	L	Χ	L	Χ	Address & control valid
n + 1	Х	Х	Х	Х	X	Х	L	X	
n + 2	Х	Х	Х	Х	Х	L	Х	Q0	Read out A0

Notes: 1. H means logical High and L means logical Low. X means Don't care. Q is data output.

(2) Burst Read Operation

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌĒ	CKE	I/O	OPERATION
n	A0	Н	Х	L	L	Х	L	Х	Address & control valid
n + 1	Х	Х	Χ	Н	Χ	Х	L	Х	
n + 2	Х	Х	X	Н	X	L	L	Q0	Read out A0
n + 3	Х	Χ	Χ	Н	Χ	L	L	Q0 + 1	Read out A0 + 1
n + 4	Х	X	X	Н	X	L	L	Q0 + 2	Read out A0 + 2
n + 5	A1	Н	Х	L	L	L	L	Q0 + 3	Read out A0 + 3
n + 6	Х	X	X	Н	X	L	L	Q0	Read out A0
n + 7	Х	X	X	Н	X	L	L	Q1	Read out A1
n + 8	A2	Н	X	L	L	L	L	Q1 + 1	Read out A1 + 1
n + 9	A3	Н	Χ	L	L	L	L	Q1 + 2	Read out A1 + 2
n + 10	Х	Х	Х	Х	Х	L	L	Q2	Read out A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. Q is data output.



(3) Write Operation

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌE	CKE	I/O	OPERATION
n	A0	L	L	L	L	Х	L	Х	Address & control valid
n + 1	Х	Х	Х	Х	Х	Х	L	Х	
n + 2	Х	Х	Х	Х	Х	Х	L	D0	Write to A0

Notes: 1. H means logical High and L means logical Low. X means Don't care. D is data input.

(4) Burst Write Operation

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌE	CKE	I/O	OPERATION
n	A0	L	L	L	L	Х	L	Х	Address & control valid
n + 1	Х	Х	L	Н	Χ	Х	L	Х	
n + 2	Х	X	L	Н	X	Х	L	D0	Write A0
n + 3	Х	X	L	Н	X	Х	L	D0 + 1	Write A0 + 1
n + 4	Х	X	L	Н	X	Х	L	D0 + 2	Write A0 + 2
n + 5	A1	L	L	L	L	Х	L	D0 + 3	Write A0 + 3
n + 6	Х	X	L	Н	X	Х	L	D0	Write A0
n + 7	Х	X	L	Н	X	Х	L	D1	Write A1
n + 8	A2	L	L	L	L	Х	L	D1 + 1	Write A1 + 1
n + 9	A3	L	L	L	L	Х	L	D1 + 2	Write A1 + 2
n + 10	Х	Х	L	Х	Х	Х	L	D2	Write A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. D is data input.

(5) Read Operation with Clock Enable

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌĒ	CKE	I/O	OPERATION
n	A0	Н	Х	L	L	Χ	L	Х	Address & control valid
n + 1	Х	Х	Х	Χ	Х	Х	Н	Х	Ignore cycle
n + 2	A1	Н	Х	L	L	Х	L	Х	Address & control valid
n + 3	Х	Χ	Х	Χ	Х	L	Н	Q0	Ignore clock, Q0 is on bus
n + 4	Х	X	Х	X	Х	L	Н	Q0	Ignore clock, Q0 is on bus
n + 5	A2	Н	Х	L	L	L	L	Q0	Read out A0
n + 6	A3	Н	Х	L	L	L	L	Q1	Read out A1
n + 7	Х	Х	Х	Х	Х	L	L	Q2	Read out A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. Q is data output.



(6) Write Operation with Clock Enable

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌĒ	CKE	I/O	OPERATION
n	A0	L	L	L	L	Х	L	Х	Address & control valid
n + 1	Х	Х	X	Х	Х	Х	Н	Х	Ignore clock
n + 2	A1	L	L	L	L	Х	L	Х	Address & control valid
n + 3	Х	Х	Х	Х	Х	Х	Н	Х	Ignore clock
n + 4	Х	Х	Χ	Х	Χ	Х	Н	Х	Ignore clock
n + 5	A2	L	L	L	L	Х	L	D0	Address & control valid
n + 6	A3	L	L	L	L	Х	L	D1	Write A1
n + 7	Х	Х	Х	Х	Х	Х	L	D2	Write A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. D is data input.

(7) Read Operation with Chip Enable

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌE	CKE	I/O	OPERATION
n	A0	Н	Χ	L	L	Х	L	Х	Address & control valid
n + 1	Х	Χ	Χ	L	Н	Х	L	Х	Deselect
n + 2	A1	Н	X	L	L	L	L	Q0	Read A0
n + 3	Х	X	Х	L	Н	Х	L	Z	Deselect
n + 4	Х	Х	Х	L	Н	L	L	Q1	Read A1
n + 5	A2	Н	Х	L	L	Х	L	Z	Deselect
n + 6	Х	Х	Х	L	Н	Х	L	Z	Deselect
n + 7	Х	Х	Х	L	Н	L	L	Q2	Read A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. Q is data output. Z means Hi-Z.

(8) Write Operation with Chip Enable

CYCLE	ADDRESS	WE	BW	ADV	CE	ŌĒ	CKE	I/O	OPERATION
n	A0	L	L	L	L	Χ	L	Х	Address & control valid
n + 1	Х	Х	Х	L	Н	Х	L	Х	Deselect
n + 2	A1	L	L	L	L	Х	L	D0	Write A0
n + 3	Х	Х	Х	L	Н	Х	L	Z	Deselect
n + 4	Х	Х	Х	L	Н	Х	L	D1	Write A1
n + 5	A2	L	L	L	L	Х	L	Z	Deselect
n + 6	Х	Х	Х	L	Н	Х	L	Z	Deselect
n + 7	Х	Х	Х	L	Н	Х	L	D2	Write A2

Notes: 1. H means logical High and L means logical Low. X means Don't care. D is data input. Z means Hi-Z.



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	-0.5 to 4.6	V
V_{DDQ}	Output Buffer Power Supply Voltage	-0.5 to V _{DD} + 0.5 (≤ 4.6 V max)	V
V _{IN}	Input Terminal Voltage	-0.5* to 4.6	V
V _{I/O}	Input/Output Terminal Voltage	-0.5* to V _{DDQ} + 0.5** (≤ 4.6 V max)	V
P _D	Power Dissipation	1.5	W
T _{solder}	Soldering Temperature (10s)	260	°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _{opr}	Operating Temperature	–10 to 85	°C

^{*:} -1.0 V with a pulse width of 20% of t_{KC} min (3 ns max)

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT
V_{DD}	Power Supply Voltage	3.135	3.3	3.465	V
V_{DDQ}	Output Buffer Power Supply Voltage	3.135	3.3	3.465	V
V _{IH}	Input High Voltage	2.0	_	V _{DD} + 0.3**	V
V _{IH1}	Input High Voltage for MODE pin	V _{DD} – 0.3	V_{DD}	V _{DD} + 0.3	V
V _{IL}	Input Low Voltage	-0.3*	_	0.8	V
V _{IL1}	Input Low Voltage for MODE and NU pins	-0.3	0.0	0.3	V

^{*:} -0.7 V with a pulse width of 20% of t_{KC} min (3 ns max)

Note: The NU pin must be low or not connected.

You must not apply a voltage of more than 0.8 V to the NU.

^{**:} V_{DDQ} + 1.0 V with a pulse width of 20% of t_{KC} min (3 ns max)

^{**:} V_{DDQ} + 0.7 V with a pulse width of 20% of t_{KC} min (3 ns max)



$\underline{DC\ CHARACTERISTICS}$ (Ta = 0° to 70°C, $V_{DD} = V_{DDQ} = 3.3\ V \pm 5$ %)

SYMBOL	PARAMETER	TEST CONDITIONS		MIN	TYP.	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 to V _{DD}		-1	_	1	μА	
I _{NU}	Input Current (NU pin)	V _{IN} = 0 to 0.3 V		-1	_	1	μА	
ILO	Output Leakage Current	Device Deselected or Output Deselecte V _{OUT} = 0 to V _{DDQ}	ed,	-1	_	1	μА	
\/ - · ·	Output High Voltage	I _{OH} = -8 mA		2.4	_	_	V	
V _{OH}	Output High Voltage	$I_{OH} = -100 \mu A$		V _{DDQ} - 0.2			V	
V _{OL}	Output Low Voltage	$I_{OL} = 8 \text{ mA}$	_		0.4	V		
VOL	Output Low Voltage	$I_{OL} = 100 \mu A$	_		0.2	V		
		$I_{OUT} = 0 \text{ mA},$	150 MHz	_		440		
I _{DDO1}	Operating Current	All Inputs = V _{DD} – 0.2 V/0.2 V	143 MHz	_		420	mA	
		Clock ≥ t _{KC} Minimum	133 MHz	_	_	400		
		Device Deselected	150 MHz	_	_	180		
I _{DDO2}	Operating Current (idle)	$I_{OUT} = 0 \text{ mA},$ All Inputs = $V_{DD} - 0.2 \text{ V}/0.2 \text{ V}$	143 MHz	_		170	mA	
		Clock ≥ t _{KC} Minimum	133 MHz	_	_	160		
I _{DDS1}	Standby Current (TTL level)	Clock = V _{SS} All Inputs = V _{IH} or V _{IL}		_	_	60	mA	
I _{DDS2}	Standby Current (MOS level)	Clock = V _{SS} All Inputs = V _{DD} - 0.2 V or 0.2 V		_	_	10	mA	
I _{DDS3}	Standby Current (Snooze Mode)	$\begin{split} ZZ &\geq V_{DD} - 0.2 \ V \\ All \ Inputs &= V_{DD} - 0.2 \ V \ or \ 0.2 \ V \\ Clock &\geq t_{KC} \ Minimum \end{split}$		_	10	mA		
I _{DDS4}	Standby Current (CKE Mode)	$\label{eq:continuous} \hline \hline \textit{CKE} & \geq \textit{V}_{IH} \\ \textit{All Inputs} = \textit{V}_{DD} - 0.2 \; \textit{V} \; \text{or} \; 0.2 \; \textit{V} \\ \textit{Clock} \geq \textit{t}_{KC} \; \textit{Minimum} \\ \hline \hline$		_	_	10	mA	

Note: Operating Current (I_{DDO1}) is specified with 50% Read cycles and 50% Write cycles.

CAPACITANCE (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITIONS	MAX	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	5	pF
C _{I/O}	Input/Output Capacitance	V _{I/O} = GND	7	pF
C _{NU}	Input Capacitance of NU	V _{IN} = GND	10	pF

Note: This parameter is periodically sampled and is not 100% tested.



<u>AC CHARACTERISTICS</u> (Ta = 0° to 70°C, $V_{DD} = V_{DDQ} = 3.3 \text{ V} \pm 5 \text{ \%}$)

				TC55V	D836FF			
SYMBOL	PARAMETER	-1	50	-1	43	-1	33	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{KC}	CLK Cycle Time	6.6	_	7.0	_	7.5	_	
t _{KH}	CLK High Pulse Width	2	_	2	_	2.3	_	
t _{KL}	CLK Low Pulse Width	2	_	2	_	2.3	_	
t _{KQV}	CLK High to Output Valid	_	3.8	_	4	_	4.2	
t _{KQX}	CLK High to Output Invalid	1.5	_	1.5	_	1.5	_	
t _{KQLZ}	CLK High to Output Low-Z	2.0	_	2.0	_	2.0	_	
t _{KQHZ}	CLK High to Output High-Z	1.5	3.5	1.5	3.5	1.5	3.5	
t _{GQV}	OE Low to Output Valid	_	4	_	4	_	4.2	
t _{GQLZ}	OE Low to Output Low-Z	1.5	_	1.5	_	1.5	_	
t _{GQHZ}	OE High to Output High-Z	1.5	4	1.5	4	1.5	4.2	
t _{AS}	Address Setup Time from CLK	2	_	2	_	2	_	
t _{DS}	Data Setup Time from CLK	1.5	_	1.5	_	1.7	_	
t _{WS}	WE Setup Time from CLK	2	_	2	_	2	_	
t _{CES}	CE Setup Time from CLK	2	_	2	_	2	_	ns
t _{ADVS}	ADV Setup Time from CLK	2	_	2	_	2	_	115
t _{BWS}	BW Setup Time from CLK	2	_	2	_	2	_	
t _{CKES}	CKE Setup Time from CLK	2	_	2	_	2	_	
t _{AH}	Address Hold Time from CLK	0.5		0.5	_	0.5	_	
t _{DH}	Data Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{WH}	WE Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{CEH}	CE Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{ADVH}	ADV Hold Time from CLK	0.5		0.5	_	0.5	_	
t _{BWH}	BW Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{CKEH}	CKE Hold Time from CLK	0.5		0.5		0.5		
t _{ZZ}	ZZ High to Input Ignored	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
t _{ZZR}	ZZ Low to Input Sampled	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
t _{ZZHZ}	ZZ High to Output High-Z	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
tzzLz	ZZ Low to Output Low-Z	0		0		0	_	

AC TEST CONDITIONS

PARAMETER	TEST CONDITION
Input Pulse Level	3.0 V/ 0.0 V
Input Pulse Rise and Fall Time	1 V/ns (20%/80%)
Input Timing Measurement Reference Level	1.5 V
Output Timing Measurement Reference Level	1.5 V
Output Load	As shown in Fig.1 and Fig.2

Fig.1:AC test load

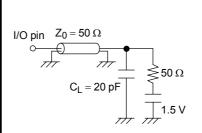
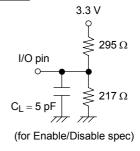


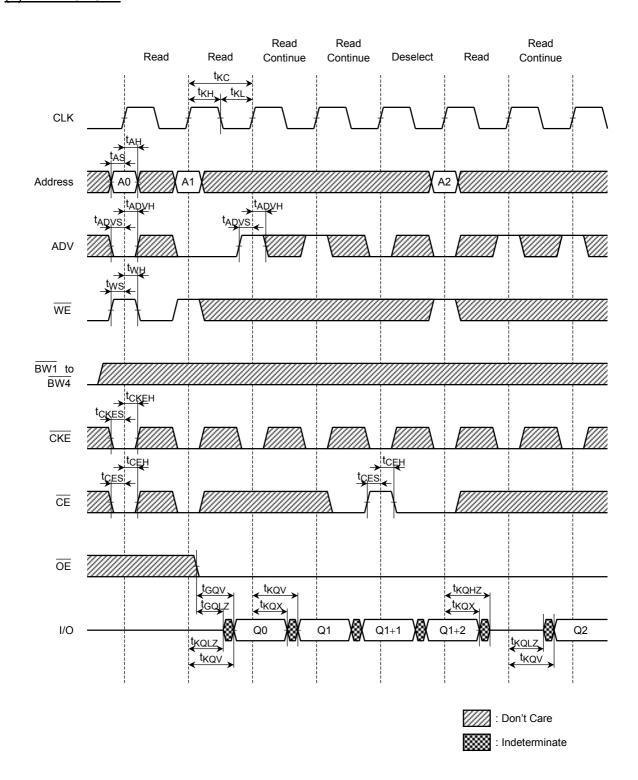
Fig.2:AC test load





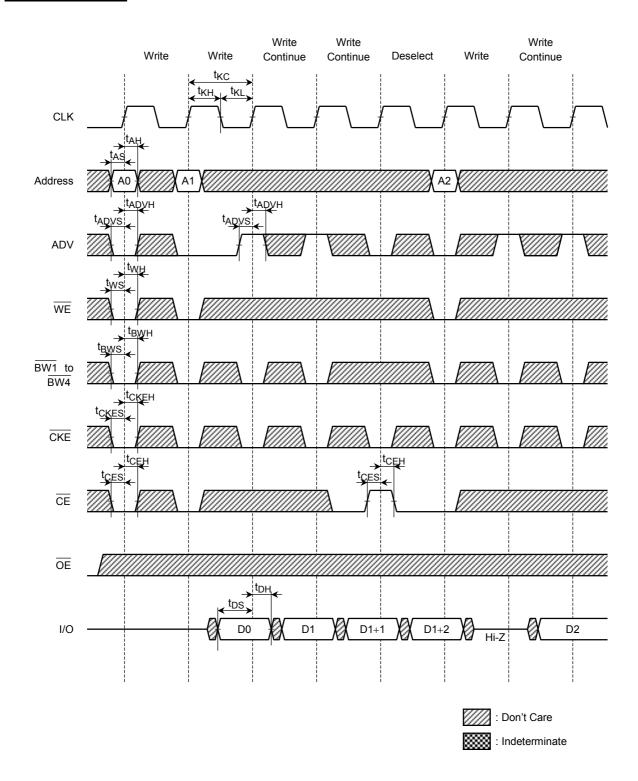
TIMING DIAGRAMS

(1) READ CYCLE



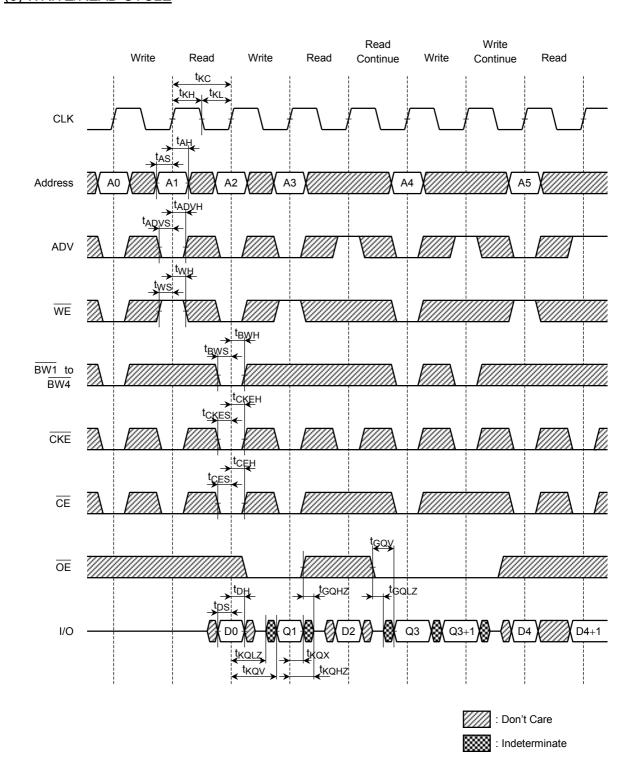


(2) WRITE CYCLE



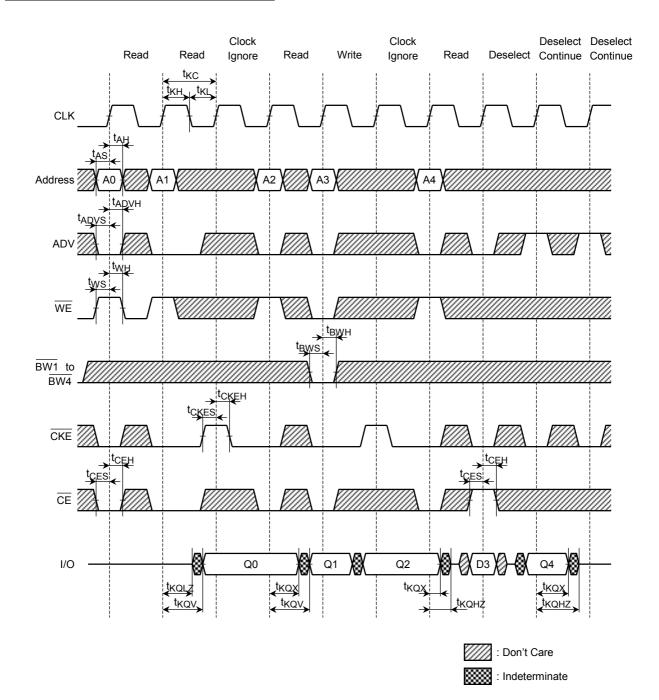


(3) WRITE/READ CYCLE



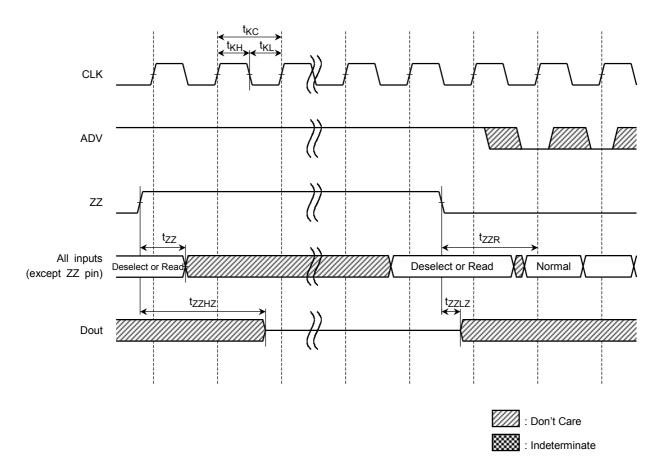


(4) CLOCK IGNORE/DESELECT CYCLE





(5) SNOOZE CYCLE

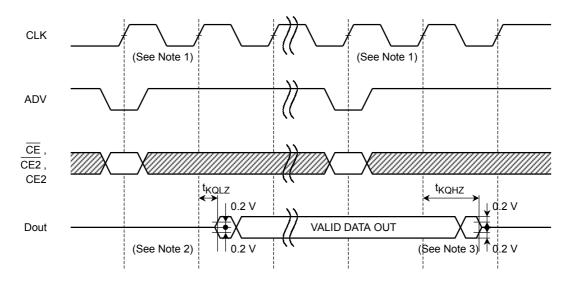


Notes: 1. The 2 cycles immediately prior to a Snooze brought about by the ZZ pin must be Read or Deselect cycles.

2. Memory data is retained during Snooze cycles.

- Notes: 1. Do not apply opposite data polarity to the I/O pins when they are in the output state.
 - 2. Output enable and output disable times are specified as follows using the output load shown in Fig.1.

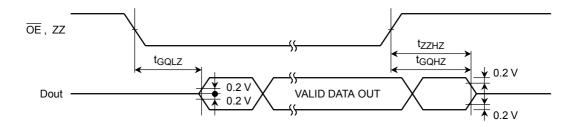
(A) tkqlz, tkqhz



Notes: 1. Input states are defined in the Synchronous Input Truth Table.

- If the device was previously deselected, when the device is selected, the output remains in a high impedance state in the present clock cycle regardless of OE because of the output enable delay register. Valid data appears in the second clock cycle when OE is low.
- 3. When the device is deselected, the output goes into a high impedance state in the next clock cycle regardless of $\overline{\text{OE}}$.

(B) t_{GQLZ}, t_{GQHZ}, t_{ZZHZ}





V_{DDQ} = 2.5 V Interface specification

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT	
V_{DD}	Power Supply Voltage	3.135	3.3	3.465	V	
V_{DDQ}	Output Buffer Power Supply Voltage	2.375	2.5	2.9	V	
V	Input High Voltage for Address and Control pins	1.7	_	V _{DD} + 0.3**	V	
V _{IH}	Input High Voltage for I/O pins	1.7	_	3.465	V	
V _{IH1}	Input High Voltage for MODE pin	V _{DD} – 0.3	V _{DD}	V _{DD} + 0.3	V	
V _{IL}	Input Low Voltage	-0.3*	_	0.7	V	
V _{IL1}	Input Low Voltage for MODE and NU pins	-0.3	0.0	0.3	V	

^{*: -0.7} V with a pulse width of 20% of t_{KC} min (3 ns max)

Note: The NU pin must be low or not connected.

You must not apply a voltage of more than 0.8 V to the NU.

DC CHARACTERISTICS (Ta = 0° to 70°C, V_{DD} = 3.3 V ± 5 %, V_{DDQ} = 2.375 V to 2.9 V)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP.	MAX	UNIT		
I _{IL}	Input Leakage Current	V _{IN} = 0 to V _{DD}	-1	_	1	μА		
I _{NU}	Input Current (NU pin)	V _{IN} = 0 to 0.3 V	-1	_	1	μА		
I _{LO}	Output Leakage Current	Device Deselected or Output Deselecte V _{OUT} = 0 to V _{DDQ}	-1	_	1	μА		
V _{OH}	Output High Voltage	I _{OH} = -2 mA		1.7			V	
		Ι _{ΟΗ} = -100 μΑ		V _{DDQ} - 0.2			v	
V _{OL}	Output Low Voltage	I _{OL} = 2 mA		_		0.7	V	
		I _{OL} = 100 μA		_		0.2		
I _{DDO1}	Operating Current	$\begin{split} &I_{OUT} = 0 \text{ mA,} \\ &\text{All Inputs} = V_{DD} - 0.2 \text{ V/0.2 V} \\ &\text{Clock} \geq t_{KC} \text{ Minimum} \end{split}$	150 MHz	_		440	mA	
			143 MHz	_		420		
			133 MHz	_		400		
I _{DDO2}	Operating Current (idle)	Device Deselected $I_{OUT} = 0$ mA, All Inputs = $V_{DD} - 0.2$ V/0.2 V Clock \geq t _{KC} Minimum	150 MHz	_		180	mA	
			143 MHz	_		170		
			133 MHz	_		160		
I _{DDS2}	Standby Current (MOS level)	Clock = V _{SS} All Inputs = V _{DD} - 0.2 V or 0.2 V		_	_	10	mA	
I _{DDS3}	Standby Current (Snooze Mode)	$\begin{split} ZZ &\geq V_{DD} - 0.2 \ V \\ \text{All Inputs} &= V_{DD} - 0.2 \ V \ \text{or} \ 0.2 \ V \\ \text{Clock} &\geq t_{KC} \ \text{Minimum} \end{split}$	_	_	10	mA		
I _{DDS4}	Standby Current (CKE Mode)	$\label{eq:controller} \begin{array}{ c c } \hline \overline{CKE} & \geq V_{IH} \\ \hline \text{All Inputs} = V_{DD} - 0.2 \text{ V or } 0.2 \text{ V} \\ \hline \text{Clock} \geq t_{KC} \text{ Minimum} \\ \hline \end{array}$	_	_	10	mA		

Note: Operating Current (I_{DDO1}) is specified with 50% Read cycles and 50% Write cycles.

^{**:} V_{DD} + 0.7 V with a pulse width of 20% of t_{KC} min (3 ns max)

^{***:} V_{DDQ} + 0.7 V with a pulse width of 20% of t_{KC} min (3 ns max)



$\underline{AC\ CHARACTERISTICS}\ (Ta=0°\ to\ 70°C,\ V_{DD}=3.3\ V\pm 5\ \%,\ V_{DDQ}=2.375\ V\ to\ 2.9\ V)$

			TC55VD836FF					
SYMBOL	PARAMETER	-150		-143		-133		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{KC}	CLK Cycle Time	6.6		7.0	_	7.5	_	
t _{KH}	CLK High Pulse Width	2		2	_	2.3	_	
t _{KL}	CLK Low Pulse Width	2		2	_	2.3	_	
t _{KQV}	CLK High to Output Valid	_	3.8	_	4		4.2	
t _{KQX}	CLK High to Output Invalid	1.5	_	1.5	_	1.5	_	
t _{KQLZ}	CLK High to Output Low-Z	2.0	_	2.0	_	2.0	_	
t _{KQHZ}	CLK High to Output High-Z	1.5	3.5	1.5	3.5	1.5	3.5	
t_{GQV}	OE Low to Output Valid	_	4	_	4	_	4.2	
t_{GQLZ}	OE Low to Output Low-Z	1.5		1.5	_	1.5	_	
t _{GQHZ}	OE High to Output High-Z	1.5	4	1.5	4	1.5	4.2	
t _{AS}	Address Setup Time from CLK	2		2	_	2	_	
t _{DS}	Data Setup Time from CLK	1.5		1.5	_	1.7	_	
t _{WS}	WE Setup Time from CLK	2		2	_	2	_	
t _{CES}	CE Setup Time from CLK	2		2	_	2		ns
t _{ADVS}	ADV Setup Time from CLK	2		2	_	2	_	115
t _{BWS}	BW Setup Time from CLK	2	_	2	_	2	_	
t _{CKES}	CKE Setup Time from CLK	2		2	_	2	_	
t _{AH}	Address Hold Time from CLK	0.5		0.5	_	0.5		
t _{DH}	Data Hold Time from CLK	0.5		0.5	_	0.5	_	
t _{WH}	WE Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{CEH}	CE Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{ADVH}	ADV Hold Time from CLK	0.5		0.5	_	0.5	_	
t _{BWH}	BW Hold Time from CLK	0.5		0.5		0.5	_	
t _{CKEH}	CKE Hold Time from CLK	0.5	_	0.5	_	0.5	_	
t _{ZZ}	ZZ High to Input Ignored	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
t _{ZZR}	ZZ Low to Input Sampled	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
t _{ZZHZ}	ZZ High to Output High-Z	0	2t _{KC}	0	2t _{KC}	0	2t _{KC}	
t _{ZZLZ}	ZZ Low to Output Low-Z	0		0		0	_	

AC TEST CONDITIONS

PARAMETER	TEST CONDITION				
Input Pulse Level	2.3 V/ 0.0 V				
Input Pulse Rise and Fall Time	1 V/ns (20%/80%)				
Input Timing Measurement Reference Level	1.15 V				
Output Timing Measurement Reference Level	1.15 V				
Output Load	As shown in Fig.1 and Fig.2				

Fig.1:AC test load

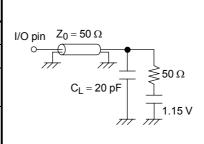
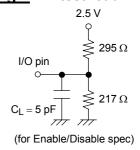
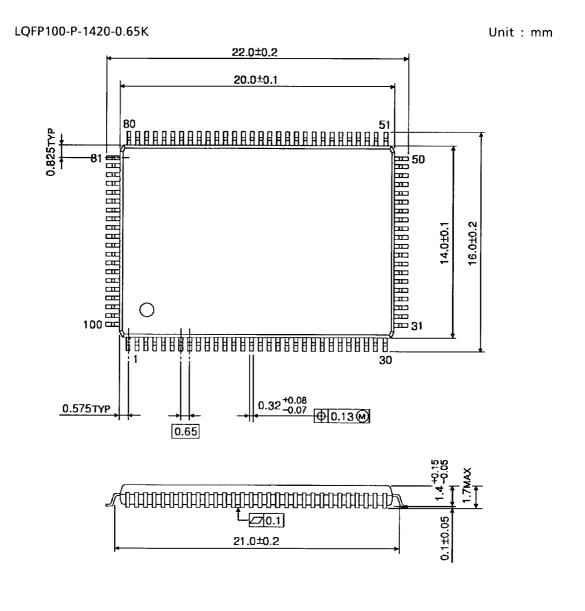


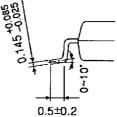
Fig.2:AC test load





PACKAGE DIMENSIONS





Weight: 0.56 g (typ)

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000707EBA

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